Stephen J Pearton

List of Publications by Citations

2,064 papers	60,210 citations	99 h-index	181 g-index
2,179 ext. papers	64,756 ext. citations	3 avg, IF	7.53 L-index

#	Paper	IF	Citations
2064	GaN: Processing, defects, and devices. *Journal of Applied Physics*, **1999**, 86, 1-78	1	1469
2063	A review of Ga2O3 materials, processing, and devices. *Applied Physics Reviews*, **2018**, 5, 011301	4.3	1114
2062	Whispering-gallery mode microdisk lasers. *Applied Physics Letters*, **1992**, 60, 289-291	1.1	1073
2061	Wide band gap ferromagnetic semiconductors and oxides. *Journal of Applied Physics*, **2003**, 93, 1-13	1	918
2060	Hydrogen in crystalline semiconductors. *Applied Physics A: Solids and Surfaces*, **1987**, 43, 153-195		865
2059	The Blue Laser Diode **2000**,		664
2058	ZnO: growth, doping & processing. *Materials Today*, **2004**, 7, 34-40	7.1	597
2057	Recent advances in processing of ZnO. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 932		585
2056	ZnO nanowire growth and devices. *Materials Science and Engineering Reports*, **2004**, 47, 1-47	10.1	484
2055	Dilute magnetic semiconducting oxides. *Semiconductor Science and Technology*, **2004**, 19, R59-R74	0.6	477
2054	Hydrogen-selective sensing at room temperature with ZnO nanorods. *Applied Physics Letters*, **2005**, 86, 243503	1.1	475
2053	Optically detected carrier confinement to one and zero dimension in GaAs quantum well wires and boxes. *Applied Physics Letters*, **1986**, 49, 1275-1277	1.1	436
2052	Hydrogen interactions with defects in crystalline solids. *Reviews of Modern Physics*, **1992**, 64, 559-617	10	417
2051	Single-electron capacitance spectroscopy of discrete quantum levels. *Physical Review Letters*, **1992**, 68, 3088-3091	1.9	408
2050	Ferromagnetism in Mn-implanted ZnO:Sn single crystals. *Applied Physics Letters*, **2003**, 82, 239-241	1.1	382
2049	Advances in wide bandgap materials for semiconductor spintronics. *Materials Science and Engineering Reports*, **2003**, 40, 137-168	10.1	375
2048	Fabrication and performance of GaN electronic devices. *Materials Science and Engineering Reports*, **2000**, 30, 55-212	10.1	373

2047	Hydrogen in Crystalline Semiconductors. *Springer Series in Materials Science*, **1992**,	0.2	372
2046	Origin of green luminescence in ZnO thin film grown by molecular-beam epitaxy. *Journal of Applied Physics*, **2005**, 98, 073502	1	351
2045	Ion implantation into GaN. *Materials Science and Engineering Reports*, **2001**, 33, 51-108	10.1	330
2044	Magnetic properties of n-GaMnN thin films. *Applied Physics Letters*, **2002**, 80, 3964-3966	1.1	310
2043	Recent progress in processing and properties of ZnO. *Superlattices and Microstructures*, **2003**, 34, 3-32	1	308
2042	Hydrogen sensing using pd-functionalized multi-layer graphene nanoribbon networks. *Advanced Materials*, **2010**, 22, 4877-80	6.6	280
2041	Ion implantation for isolation of III-V semiconductors. *Materials Science and Engineering Reports*, **1990**, 4, 313-363		265
2040	Perspective: Opportunities and Future Directions for Ga2O3. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P356-P359	0.7	261
2039	Magnetic and structural properties of Mn-implanted GaN. *Applied Physics Letters*, **2001**, 78, 3475-3477	1.1	256
2038	Ion implantation doping and isolation of GaN. *Applied Physics Letters*, **1995**, 67, 1435-1437	1.1	250
2037	Indication of ferromagnetism in molecular-beam-epitaxy-derived N-type GaMnN. *Applied Physics Letters*, **2001**, 79, 1312-1314	1.1	249
2036	Perspective: Ga2O3 for ultra-high power rectifiers and MOSFETS. *Journal of Applied Physics*, **2018**, 124, 220901	1	245
2035	Hydrogen sensing at room temperature with Pt-coated ZnO thin films and nanorods. *Applied Physics Letters*, **2005**, 87, 222106	1.1	244
2034	Ferromagnetism in cobalt-implanted ZnO. *Applied Physics Letters*, **2003**, 83, 5488-5490	1.1	241
2033	Donor neutralization in GaAs(Si) by atomic hydrogen. *Applied Physics Letters*, **1985**, 47, 108-110	1.1	214
2032	Recent advances in wide bandgap semiconductor biological and gas sensors. *Progress in Materials Science*, **2010**, 55, 1-59	12.7	212
2031	Depletion-mode ZnO nanowire field-effect transistor. *Applied Physics Letters*, **2004**, 85, 2274-2276	1.1	208
2030	Unconventional carrier-mediated ferromagnetism above room temperature in ion-implanted (Ga, Mn)P:C. *Physical Review Letters*, **2002**, 89, 107203	1.9	207

2029	GaN-based diodes and transistors for chemical, gas, biological and pressure sensing. *Journal of Physics Condensed Matter*, **2004**, 16, R961-R994	0.7	206
2028	Threshold characteristics of semiconductor microdisk lasers. *Applied Physics Letters*, **1993**, 63, 1310-1312	1.1	203
2027	Effect of temperature on Ga2O3(Gd2O3)/GaN metal□xide□emiconductor field-effect transistors. *Applied Physics Letters*, **1998**, 73, 3893-3895	1.1	199
2026	Ultrahigh doping of GaAs by carbon during metalorganic molecular beam epitaxy. *Applied Physics Letters*, **1989**, 55, 1750-1752	1.1	196
2025	p-type behavior in phosphorus-doped (Zn,Mg)O device structures. *Applied Physics Letters*, **2004**, 84, 3474-3476	1.1	192
2024	Donor-hydrogen complexes in passivated silicon. *Physical Review B*, **1988**, 37, 2770-2773	1	190
2023	Hydrogen incorporation and diffusivity in plasma-exposed bulk ZnO. *Applied Physics Letters*, **2003**, 82, 385-387	1.1	186
2022	GaN Electronics. *Advanced Materials*, **2000**, 12, 1571-1580	6.6	186
2021	Review□onizing Radiation Damage Effects on GaN Devices. *ECS Journal of Solid State Science and Technology*, **2016**, 5, Q35-Q60	0.7	182
2020	1.54-□m photoluminescence from Er-implanted GaN and AlN. *Applied Physics Letters*, **1994**, 65, 992-994	1.1	178
2019	Electrical effects of plasma damage in p-GaN. *Applied Physics Letters*, **1999**, 75, 2569-2571	1.1	170
2018	Electrical characteristics of Au and Ag Schottky contacts on n-ZnO. *Applied Physics Letters*, **2003**, 83, 1575-1577	1.1	168
2017	Ca and O ion implantation doping of GaN. *Applied Physics Letters*, **1996**, 68, 1945-1947	1.1	167
2016	Inductively coupled plasma etching of GaN. *Applied Physics Letters*, **1996**, 69, 1119-1121	1.1	166
2015	Effects of high-dose Mn implantation into ZnO grown on sapphire. *Applied Physics Letters*, **2004**, 84, 2292-2294	1.1	162
2014	Kinetics of implantation enhanced interdiffusion of Ga and Al at GaAs-GaxAl1□As interfaces. *Applied Physics Letters*, **1986**, 49, 223-225	1.1	162
2013	Hydrogenation of shallow-donor levels in GaAs. *Journal of Applied Physics*, **1986**, 59, 2821-2827	1	159
2012	A survey of ohmic contacts to III-V compound semiconductors. *Thin Solid Films*, **1997**, 308-309, 599-606	0.7	157

2011	MgZnO□AlGaN heterostructure light-emitting diodes. *Applied Physics Letters*, **2004**, 85, 4272	1.1	153
2010	Influence of MgO and Sc2O3 passivation on AlGaN/GaN high-electron-mobility transistors. *Applied Physics Letters*, **2002**, 80, 1661-1663	1.1	153
2009	Ion-implanted GaN junction field effect transistor. *Applied Physics Letters*, **1996**, 68, 2273-2275	1.1	153
2008	Structure and magnetism of cobalt-doped ZnO thin films. *New Journal of Physics*, **2008**, 10, 065002	0.8	150
2007	Hydrogen local modes and shallow donors in ZnO. *Physical Review B*, **2005**, 72,	1	149
2006	A Review of Dry Etching of GaN and Related Materials. *MRS Internet Journal of Nitride Semiconductor Research*, **2000**, 5, 1		148
2005	Directional light coupling from microdisk lasers. *Applied Physics Letters*, **1993**, 62, 561-563	1.1	148
2004	Review of radiation damage in GaN-based materials and devices. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2013**, 31, 050801	0.9	145
2003	Radiation effects in GaN materials and devices. *Journal of Materials Chemistry C*, **2013**, 1, 877-887	2.2	139
2002	Transport properties of phosphorus-doped ZnO thin films. *Applied Physics Letters*, **2003**, 83, 1128-1130	1.1	139
2001	Electrical transport properties of single ZnO nanorods. *Applied Physics Letters*, **2004**, 85, 2002-2004	1.1	138
2000	Carbon nanotube films for room temperature hydrogen sensing. *Nanotechnology*, **2005**, 16, 2218-21	1.2	132
1999	ZnO spintronics and nanowire devices. *Journal of Electronic Materials*, **2006**, 35, 862-868	0.7	131
1998	Wet chemical etching of AlN. *Applied Physics Letters*, **1995**, 67, 1119-1121	1.1	131
1997	pH measurements with single ZnO nanorods integrated with a microchannel. *Applied Physics Letters* , **2005**, 86, 112105	1.1	127
1996	Vibrational characteristics of acceptor-hydrogen complexes in silicon. *Applied Physics Letters*, **1987**, 50, 1086-1088	1.1	124
1995	Room temperature deposited indium zinc oxide thin film transistors. *Applied Physics Letters*, **2007**, 90, 232103	1.1	122
1994	Hidden hydrogen□ in as-grown ZnO. *Applied Physics Letters*, **2004**, 85, 5601-5603	1.1	122

1993	. *IEEE Transactions on Electron Devices*, **2007**, 54, 1040-1048	0.9	121
1992	Electroluminescence from ZnO nanowire/polymer composite p-n junction. *Applied Physics Letters*, **2006**, 88, 173503	1.1	121
1991	Depth and thermal stability of dry etch damage in GaN Schottky diodes. *Applied Physics Letters*, **1999**, 75, 232-234	1.1	120
1990	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga2O3. *Applied Physics Letters*, **2017**, 110, 192101	1.1	118
1989	Pt⍰nO nanowire Schottky diodes. *Applied Physics Letters*, **2004**, 85, 3107-3109	1.1	116
1988	Low bias electron cyclotron resonance plasma etching of GaN, AlN, and InN. *Applied Physics Letters*, **1994**, 64, 2294-2296	1.1	116
1987	2300V Reverse Breakdown Voltage Ga2O3Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2018**, 7, Q92-Q96	0.7	116
1986	High Breakdown Voltage (⍰01) $beta $ -Ga2O3 Schottky Rectifiers. *IEEE Electron Device Letters*, **2017**, 38, 906-909	1.5	114
1985	Effects of ambient atmosphere on the transfer characteristics and gate-bias stress stability of amorphous indium-gallium-zinc oxide thin-film transistors. *Applied Physics Letters*, **2010**, 96, 102107	1.1	114
1984	CCl4 doping of GaN grown by metalorganic molecular beam epitaxy. *Applied Physics Letters*, **1995**, 66, 1969-1971	1.1	114
1983	Damage to epitaxial GaN layers by silicon implantation. *Applied Physics Letters*, **1996**, 69, 2364-2366	1.1	110
1982	Room temperature operation of microdisc lasers with submilliamp threshold current. *Electronics Letters*, **1992**, 28, 1010-1012	0.4	110
1981	Flexible graphene-based chemical sensors on paper substrates. *Physical Chemistry Chemical Physics*, **2013**, 15, 1798-801	1.1	109
1980	Contacts to ZnO. *Journal of Crystal Growth*, **2006**, 287, 149-156	0.6	109
1979	AlGaN/GaN metal⍰xide⍰emiconductor high electron mobility transistors using Sc2O3 as the gate oxide and surface passivation. *Applied Physics Letters*, **2003**, 82, 2530-2532	1.1	109
1978	Hydrogen passivation of gold-related deep levels in silicon. *Physical Review B*, **1982**, 26, 7105-7108	1	108
1977	Electrical detection of immobilized proteins with ungated AlGaN⍰aN high-electron-mobility Transistors. *Applied Physics Letters*, **2005**, 87, 023508	1.1	107
1976	Oxygen and zinc vacancies in as-grown ZnO single crystals. *Journal Physics D: Applied Physics*, **2009**, 42, 175411	1	106

1975	Wide bandgap GaN-based semiconductors for spintronics. *Journal of Physics Condensed Matter*, **2004**, 16, R209-R245	0.7	106
1974	Thermal stability of W ohmic contacts to n-type GaN. *Journal of Applied Physics*, **1996**, 80, 278-281	1	106
1973	Enzymatic glucose detection using ZnO nanorods on the gate region of AlGaN□GaN high electron mobility transistors. *Applied Physics Letters*, **2007**, 91, 252103	1.1	105
1972	Vibrational spectroscopy of acceptor-hydrogen complexes in silicon: Evidence for low-frequency excitations. *Physical Review B*, **1988**, 37, 8313-8318	1	102
1971	High-density plasma etching of compound semiconductors. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1997**, 15, 633-637	0.9	101
1970	Electrical detection of biomaterials using AlGaN/GaN high electron mobility transistors. *Journal of Applied Physics*, **2008**, 104, 031101	1	101
1969	High performance indium gallium zinc oxide thin film transistors fabricated on polyethylene terephthalate substrates. *Applied Physics Letters*, **2008**, 93, 082102	1.1	101
1968	Ferromagnetism in Mn- and Co-implanted ZnO nanorods. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2003**, 21, 1476		100
1967	Carbon doping of III□V compounds grown by MOMBE. *Journal of Crystal Growth*, **1990**, 105, 375-382	0.6	100
1966	UV photoresponse of single ZnO nanowires. *Applied Physics A: Materials Science and Processing*, **2005**, 80, 497-499	0.9	98
1965	dc and rf performance of proton-irradiated AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2001**, 79, 2196-2198	1.1	98
1964	Passivation of deep level defects in molecular beam epitaxial GaAs by hydrogen plasma exposure. *Applied Physics Letters*, **1986**, 49, 1098-1100	1.1	98
1963	Electrical and structural analysis of high-dose Si implantation in GaN. *Applied Physics Letters*, **1997**, 70, 2729-2731	1.1	97
1962	Pressure-induced changes in the conductivity of AlGaN□GaN high-electron mobility-transistor membranes. *Applied Physics Letters*, **2004**, 85, 2962-2964	1.1	97
1961	Oxygen sensors made by monolayer graphene under room temperature. *Applied Physics Letters*, **2011**, 99, 243502	1.1	96
1960	High temperature electron cyclotron resonance etching of GaN, InN, and AlN. *Applied Physics Letters*, **1995**, 66, 1761-1763	1.1	96
1959	Hydrogen motion in defect complexes: Reorientation kinetics of the B-H complex in silicon. *Physical Review Letters*, **1988**, 61, 2786-2789	1.9	96
1958	Lattice location of deuterium interacting with the boron acceptor in silicon. *Physical Review Letters*, **1988**, 60, 321-324	1.9	95

1957	Growth of high quality AlGaAs by metalorganic molecular beam epitaxy using trimethylamine alane. *Applied Physics Letters*, **1990**, 56, 2654-2656	1.1	94
1956	Functionalizing Zn- and O-terminated ZnO with thiols. *Journal of Applied Physics*, **2007**, 101, 104514	1	93
1955	MgO/p-GaN enhancement mode metal-oxide semiconductor field-effect transistors. *Applied Physics Letters*, **2004**, 84, 2919-2921	1.1	93
1954	Hydrogen detection using platinum coated graphene grown on SiC. *Sensors and Actuators B: Chemical*, **2011**, 157, 500-503	3.4	92
1953	Magnetic and structural properties of Co, Cr, V ion-implanted GaN. *Journal of Applied Physics*, **2003**, 93, 4512-4516	1	91
1952	Hydrogen and ozone gas sensing using multiple ZnO nanorods. *Applied Physics A: Materials Science and Processing*, **2005**, 80, 1029-1032	0.9	91
1951	Thermal stability of ion-implanted hydrogen in ZnO. *Applied Physics Letters*, **2002**, 81, 3996-3998	1.1	91
1950	Radiation damage effects in Ga2O3 materials and devices. *Journal of Materials Chemistry C*, **2019**, 7, 10-24	2.2	90
1949	Single Wall Carbon Nanotubes for p-Type Ohmic Contacts to GaN Light-Emitting Diodes. *Nano Letters*, **2004**, 4, 911-914	3.2	90
1948	Passivation of Si donors and DX centers in AlGaAs by hydrogen plasma exposure. *Applied Physics Letters*, **1987**, 50, 921-923	1.1	90
1947	Quasi-two-dimensional β-gallium oxide solar-blind photodetectors with ultrahigh responsivity. *Journal of Materials Chemistry C*, **2016**, 4, 9245-9250	2.2	89
1946	Fabrication of p-channel thin-film transistors using CuO active layers deposited at low temperature. *Applied Physics Letters*, **2010**, 97, 222109	1.1	89
1945	Gd2O3/GaN metal-oxide-semiconductor field-effect transistor. *Applied Physics Letters*, **2000**, 77, 3230-3232	1.1	89
1944	High-Performance Indium Gallium Zinc Oxide Transparent Thin-Film Transistors Fabricated by Radio-Frequency Sputtering. *Journal of the Electrochemical Society*, **2008**, 155, H383	1.3	87
1943	Plasma etching of III–V semiconductors in CH4/H2/Ar electron cyclotron resonance discharges. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1990**, 8, 596		87
1942	Ferromagnetism in Co- and Mn-doped ZnO. *Solid-State Electronics*, **2003**, 47, 2231-2235	0.6	86
1941	Dry Etching of Electronic Oxides, Polymers, and Semiconductors. *Plasma Processes and Polymers*, **2005**, 2, 16-37	1.1	86
1940	GaN electronics for high power, high temperature applications. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 227-231	1.3	86

1939	Lateral AlxGa1−xN power rectifiers with 9.7 kV reverse breakdown voltage. *Applied Physics Letters*, **2001**, 78, 823-825	1.1	85
1938	Characteristics of MgO/GaN gate-controlled metal–oxide–semiconductor diodes. *Applied Physics Letters*, **2002**, 80, 4555-4557	1.1	85
1937	Dry and wet etching characteristics of InN, AlN, and GaN deposited by electron cyclotron resonance metalorganic molecular beam epitaxy. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1993**, 11, 1772-1775	0.9	85
1936	Room temperature hydrogen detection using Pd-coated GaN nanowires. *Applied Physics Letters*, **2008**, 93, 072109	1.1	84
1935	Dry etch damage in InN, InGaN, and InAlN. *Applied Physics Letters*, **1995**, 67, 2329-2331	1.1	84
1934	Advances in ZnO-based materials for light emitting diodes. *Current Opinion in Chemical Engineering*, **2014**, 3, 51-55	2.6	82
1933	Effect of external strain on the conductivity of AlGaN/GaN high-electron-mobility transistors. *Applied Physics Letters*, **2003**, 83, 4845-4847	1.1	82
1932	Sputtered AlN encapsulant for high-temperature annealing of GaN. *Applied Physics Letters*, **1996**, 69, 538-540	1.1	82
1931	Zn0.9Mg0.1O/ZnOp–n junctions grown by pulsed-laser deposition. *Applied Physics Letters*, **2004**, 85, 1169-1171	1.1	81
1930	Phosphorus doped ZnO light emitting diodes fabricated via pulsed laser deposition. *Applied Physics Letters*, **2008**, 92, 112108	1.1	80
1929	Ferromagnetism in Transition-Metal Doped ZnO. *Journal of Electronic Materials*, **2007**, 36, 462-471	0.7	80
1928	Electrical detection of deoxyribonucleic acid hybridization with AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2006**, 89, 122102	1.1	80
1927	Prostate specific antigen detection using AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2007**, 91, 112106	1.1	80
1926	AlGaN/GaN-based metal–oxide–semiconductor diode-based hydrogen gas sensor. *Applied Physics Letters*, **2004**, 84, 1123-1125	1.1	80
1925	Indication of hysteresis in AlMnN. *Applied Physics Letters*, **2003**, 83, 1758-1760	1.1	80
1924	ION IMPLANTATION IN III–V SEMICONDUCTOR TECHNOLOGY. *International Journal of Modern Physics B*, **1993**, 07, 4687-4761	0.5	80
1923	Evidence for the existence of a negatively charged hydrogen species in plasma-treated n-type Si. *Applied Physics Letters*, **1990**, 56, 949-951	1.1	80
1922	Structure of acceptor-hydrogen and donor-hydrogen complexes in silicon from uniaxial stress studies. *Physical Review B*, **1988**, 38, 9643-9648	1	80

1921	Advances in Hydrogen, Carbon Dioxide, and Hydrocarbon Gas Sensor Technology Using GaN and ZnO-Based Devices. *Sensors*, **2009**, 9, 4669-94	1.5	79
1920	Growth and fabrication of GaN/AlGaN heterojunction bipolar transistor. *Applied Physics Letters*, **1999**, 74, 2702-2704	1.1	79
1919	Plasma and wet chemical etching of In0.5Ga0.5P. *Journal of Electronic Materials*, **1992**, 21, 441-445	0.7	79
1918	Implant-induced high-resistivity regions in InP and InGaAs. *Journal of Applied Physics*, **1989**, 66, 656-662	1	79
1917	Ion implantation damage and annealing in InAs, GaSb, and GaP. *Journal of Applied Physics*, **1988**, 64, 629-636		79
1916	Effect of front and back gates on □Ga2O3 nano-belt field-effect transistors. *Applied Physics Letters*, **2016**, 109, 062102	1.1	79
1915	Wide Bandgap Semiconductor One-Dimensional Nanostructures for Applications in Nanoelectronics and Nanosensors. *Nanomaterials and Nanotechnology*, **2013**, 3, 1	1.3	78
1914	High mobility InGaZnO4 thin-film transistors on paper. *Applied Physics Letters*, **2009**, 94, 072103	1.1	78
1913	Bulk acceptor compensation produced in p-type silicon at near-ambient temperatures by a H2O plasma. *Applied Physics Letters*, **1984**, 44, 606-608	1.1	78
1912	Hydrogen sensing with Pt-functionalized GaN nanowires. *Sensors and Actuators B: Chemical*, **2009**, 140, 196-199	3.4	77
1911	Temperature-dependent characteristics of Pt Schottky contacts on n-type ZnO. *Applied Physics Letters*, **2004**, 84, 2835-2837	1.1	77
1910	Influence of High-Energy Proton Irradiation on □GaO Nanobelt Field-Effect Transistors. *ACS Applied Materials & Interfaces*, **2017**, 9, 40471-40476	3.1	76
1909	Breakdown voltage and reverse recovery characteristics of free-standing GaN Schottky rectifiers. *IEEE Transactions on Electron Devices*, **2002**, 49, 32-36	0.9	76
1908	The electrical properties of deep copper- and nickel-related centers in silicon. *Journal of Applied Physics*, **1983**, 54, 1375-1379	1	75
1907	Gadolinium Oxide and Scandium Oxide: Gate Dielectrics for GaN MOSFETs. *Physica Status Solidi A*, **2001**, 188, 239-242		74
1906	Magnetization dependence on electron density in epitaxial ZnO thin films codoped with Mn and Sn. *Journal of Applied Physics*, **2005**, 97, 053904	1	73
1905	Proton implantation effects on electrical and recombination properties of undoped ZnO. *Journal of Applied Physics*, **2003**, 94, 2895-2900	1	73
1904	Thermal stability of implanted dopants in GaN. *Applied Physics Letters*, **1995**, 66, 2238-2240	1.1	73

1903	Patterning of AlN, InN, and GaN in KOH-based solutions. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1996**, 14, 836-839	0.9	73
1902	Point defect induced degradation of electrical properties of Ga2O3 by 10 MeV proton damage. *Applied Physics Letters*, **2018**, 112, 032107	1.1	72
1901	Effects of interfacial oxides on Schottky barrier contacts to n- and p-type GaN. *Applied Physics Letters*, **1999**, 75, 4130-4132	1.1	72
1900	GaAs/AlGaAs microdisk lasers. *Applied Physics Letters*, **1994**, 64, 1911-1913	1.1	72
1899	Hydrogen in carbon-doped GaAs grown by metalorganic molecular beam epitaxy. *Applied Physics Letters*, **1990**, 57, 2561-2563	1.1	72
1898	Hydrogen injection and neutralization of boron acceptors in silicon boiled in water. *Applied Physics Letters*, **1986**, 48, 590-592	1.1	72
1897	Band gap properties of Zn1⊠CdxO alloys grown by molecular-beam epitaxy. *Applied Physics Letters* , **2006**, 89, 151909	1.1	71
1896	Inductively coupled plasma-induced etch damage of GaN p-n junctions. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2000**, 18, 1139-1143	0.9	71
1895	Annealing of ion implanted gallium nitride. *Applied Physics Letters*, **1998**, 72, 1190-1192	1.1	71
1894	Improved performance of quantum well infrared photodetectors using random scattering optical coupling. *Applied Physics Letters*, **1994**, 64, 960-962	1.1	71
1893	Hydrogen passivation of acceptors in p-InP. *Journal of Applied Physics*, **1989**, 66, 1993-1996	1	71
1892	Magnetic and structural properties of Fe, Ni, and Mn-implanted SiC. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2002**, 20, 579-582	0.9	70
1891	Room-temperature lasing action in In0.51Ga0.49P/In0.2Ga0.8As microcylinder laser diodes. *Applied Physics Letters*, **1993**, 62, 2021-2023	1.1	70
1890	Ion implantation in GaAs. *Nuclear Instruments & Methods in Physics Research B*, **1987**, 19-20, 369-380	0.5	70
1889	Optical and magnetic properties of Eu-doped GaN. *Applied Physics Letters*, **2006**, 89, 132119	1.1	69
1888	Reversible barrier height changes in hydrogen-sensitive Pd/GaN and Pt/GaN diodes. *Applied Physics Letters*, **2003**, 82, 739-741	1.1	69
1887	Room temperature operation of submicrometre radius disk laser. *Electronics Letters*, **1993**, 29, 1666	0.4	69
1886	Stability of carbon and beryllium-doped base GaAs/AlGaAs heterojunction bipolar transistors. *Applied Physics Letters*, **1991**, 59, 3613-3615	1.1	69

1885	Low-voltage indium gallium zinc oxide thin film transistors on paper substrates. *Applied Physics Letters*, **2010**, 96, 053510	1.1	68
1884	Ultrahigh Si+ implant activation efficiency in GaN using a high-temperature rapid thermal process system. *Applied Physics Letters*, **1998**, 73, 229-231	1.1	68
1883	Synthesis and microstructure of vertically aligned ZnO nanowires grown by high-pressure-assisted pulsed-laser deposition. *Journal of Materials Science*, **2008**, 43, 6925-6932	1.6	68
1882	Detection of hydrogen at room temperature with catalyst-coated multiple ZnO nanorods. *Applied Physics A: Materials Science and Processing*, **2005**, 81, 1117-1119	0.9	68
1881	Hydrogenation of GaN, AlN, and InN. *Applied Physics Letters*, **1994**, 64, 2724-2726	1.1	68
1880	Deep level, quenched-in defects in silicon doped with gold, silver, iron, copper or nickel. *Journal of Physics C: Solid State Physics*, **1983**, 16, 1665-1673		68
1879	The promise and perils of wide-bandgap semiconductor nanowires for sensing, electronic, and photonic applications. *Small*, **2007**, 3, 1144-50	3.3	67
1878	Carrier concentration dependence of Ti/Al/Pt/Au contact resistance on n-type ZnO. *Applied Physics Letters*, **2004**, 84, 544-546	1.1	67
1877	Influence of 60Co □rays on dc performance of AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2002**, 80, 604-606	1.1	67
1876	High voltage GaN Schottky rectifiers. *IEEE Transactions on Electron Devices*, **2000**, 47, 692-696	0.9	67
1875	Hydrogen diffusion in crystalline semiconductors. *Physica B: Condensed Matter*, **1991**, 170, 85-97	0.9	67
1874	High quality AlxGa1□As grown by organometallic vapor phase epitaxy using trimethylamine alane as the aluminum precursor. *Applied Physics Letters*, **1991**, 58, 77-79	1.1	67
1873	Low temperature (. *Applied Physics Letters*, **2007**, 90, 083104	1.1	66
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